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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Hattangady et al.	Art Unit:	2815
Serial No.:	10/783,081	Examiner:	Richards, N.
Filing Date:	02/19/2004	Docket No.:	TI-31017.1
Customer No.:	23494	Conf. No.:	6261
Title: SEMICONDUCTOR WITH A NITRIDED SILICON GATE OXIDE AND METHOD			

CERTIFICATION OF FACSIMILE TRANSMISSION

I hereby certify that the following papers are being transmitted by facsimile to the U.S. Patent and Trademark Office at 703-872-9306 on the date shown below:



Jacqueline J. Garner, Reg. No. 36,144

May 24, 2005

Date

FACSIMILE COVER SHEET

<input checked="" type="checkbox"/> FACSIMILE COVER SHEET	<input checked="" type="checkbox"/> AMENDMENT (5 Pages)
<input type="checkbox"/> NEW APPLICATION	<input checked="" type="checkbox"/> EOT 3mth (2 Pages)
<input type="checkbox"/> DECLARATION (# Pages)	<input type="checkbox"/> NOTICE OF APPEAL (# Pages)
<input type="checkbox"/> ASSIGNMENT (# Pages)	<input type="checkbox"/> APPEAL (# Pages)
<input type="checkbox"/> FORMAL DRAWINGS	<input type="checkbox"/> ISSUE FEE (# Pages)
<input type="checkbox"/> INFORMAL DRAWINGS	<input type="checkbox"/> REPLY BRIEF (IN TRIPPLICATE) (# Pages)
<input type="checkbox"/> CONTINUATION APP'N (# Pages)	
<input type="checkbox"/> DIVISIONAL APPN	
NAME OF INVENTOR(S): Hattangady	
TITLE OF INVENTION: Semiconductor with a Nitrided ...	
TI FILE NO.: TI-31017.1	DEPOSIT ACCT. NO.: 20-0668
FAXED: 5/24/2005 DUE: 2/28/2005 ATTY/SEC'Y: JJG	
RECEIPT DATE & SERIAL NO.: Serial No.: 10/783,081 Filing Date: 2/19/2004 Conf. No.: 6261	
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AMENDMENT UNDER 37 CFR 1.111

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

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Jacqueline J. Garner
Reg. No. 36,144

Dear Sir:

The following amendments and remarks are offered in response to the Examiner's Office Action dated 11/30/2004. They are respectfully submitted as a full and complete response to that Action.

Please amend the above-referenced application as follows:

There are no **Amendments to the Specification**.

Amendments to the Claims are reflected in the listing of claims that begin on page 2 of this paper.

There are no **Amendments to the Drawings**.

The **Remarks** begin on page 4.